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**Dennison**

[11] E

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[45] **Reissued Date of Patent: Sep. 14, 1999**

[54] **METHOD FOR FABRICATION OF  
CLOSE-TOLERANCE LINES AND SHARP  
EMISSION TIPS ON A SEMICONDUCTOR  
WAFER**

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[21] Appl. No.: **08/687,785**

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[22] Filed: **Jul. 19, 1996**

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Reissue of:

[64] Patent No.: **5,330,879**  
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Appl. No.: **07/914,804**  
Filed: **Jul. 16, 1992**

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[51] **Int. Cl.<sup>6</sup>** ..... **G03C 5/00**

[57] **ABSTRACT**

[52] **U.S. Cl.** ..... **430/313**; 430/314; 430/323;  
430/324; 737/228; 737/229; 737/241; 737/243

A method for fabricating submicron lines over a semicon-  
ductor material by creating a narrow hard mask over the  
material using a narrow void-producing process. The narrow  
void is thus used as a mask to form lines that are narrower  
than those that can be produced by current lithography  
techniques. The method can also be used to create sharp  
emission tips for field effect display devices.

[58] **Field of Search** ..... 430/313, 314,  
430/323, 324; 437/228, 229, 241, 243,  
67

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**72 Claims, 4 Drawing Sheets**

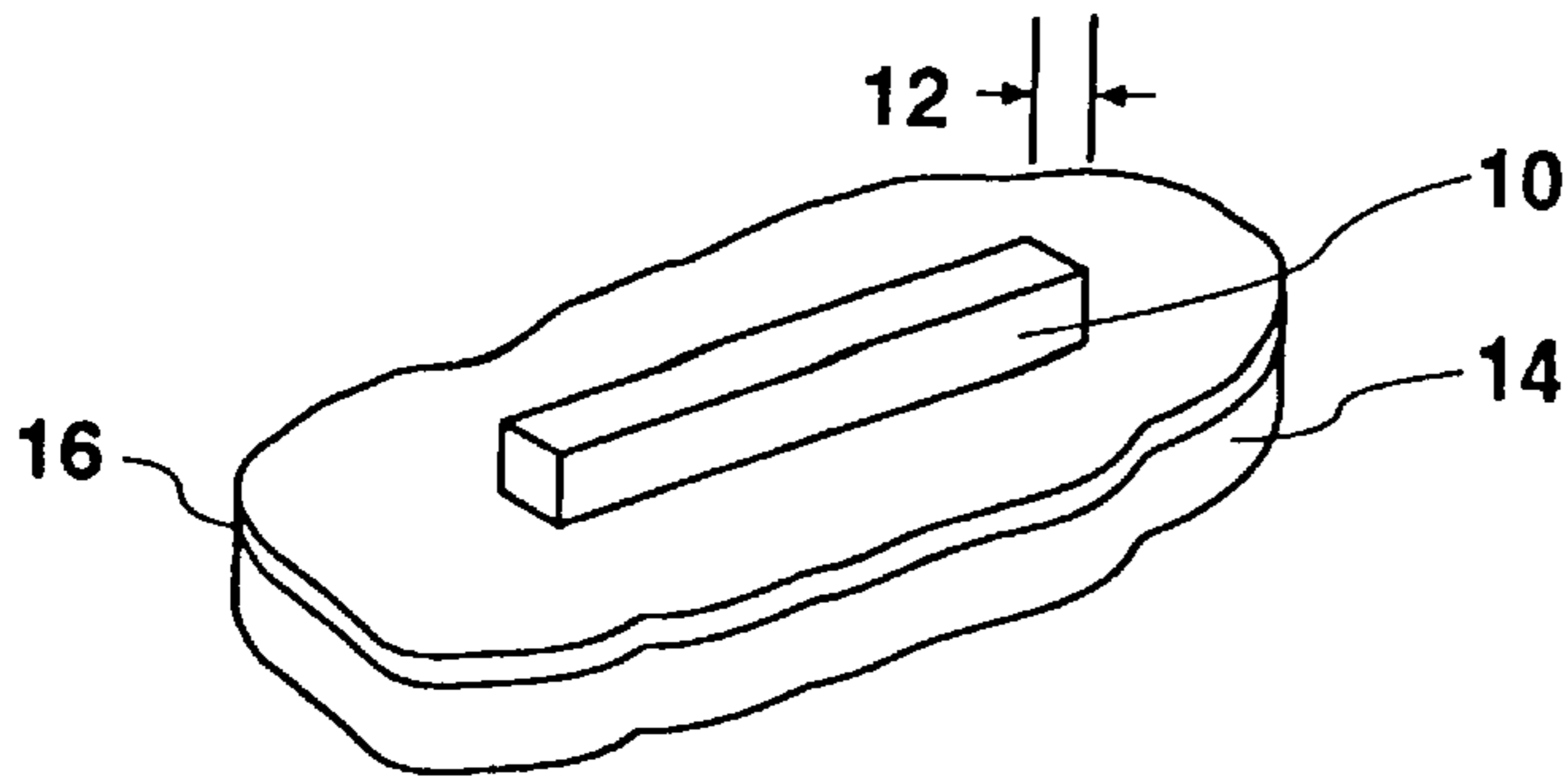


FIG 1

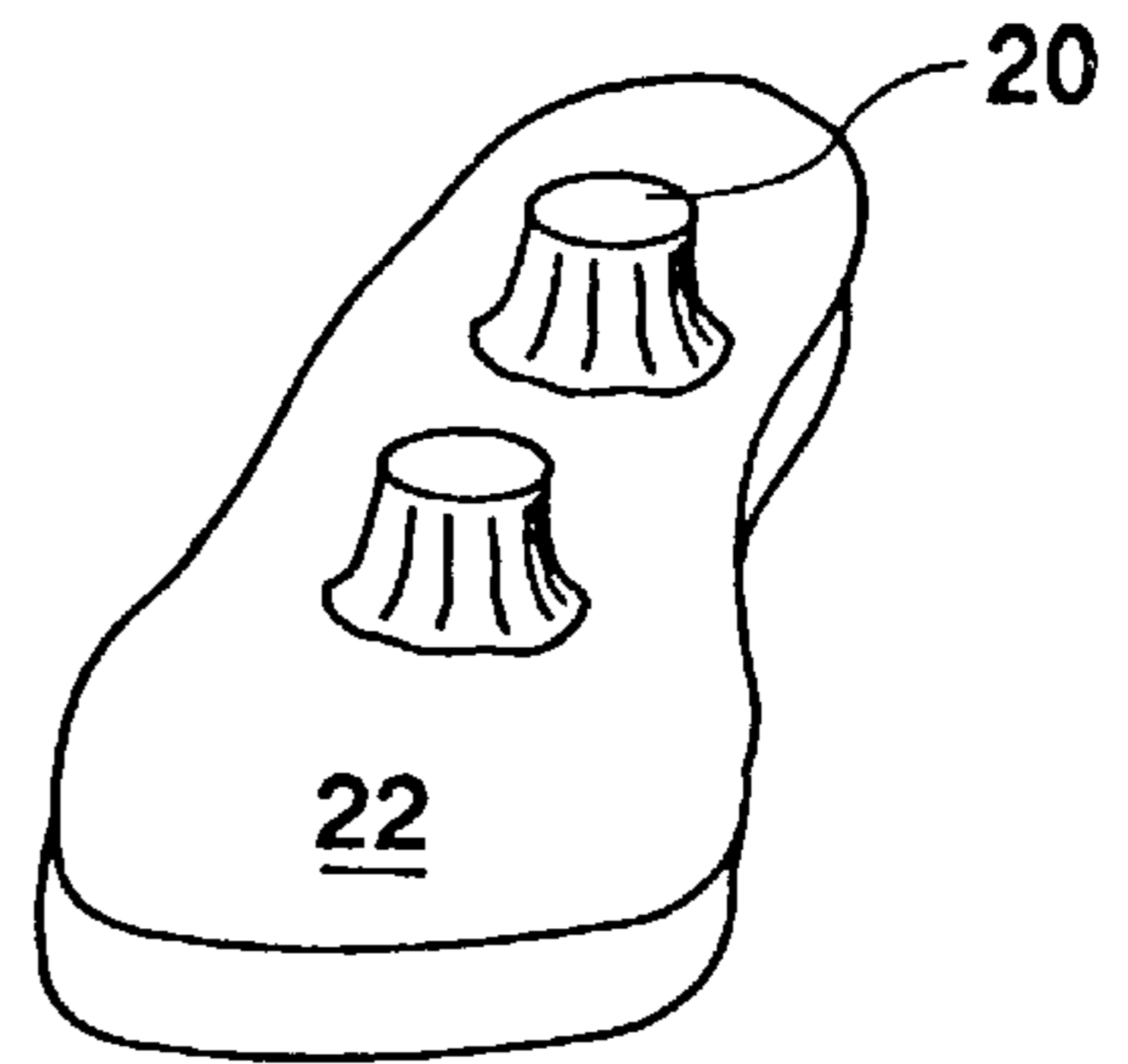


FIG 2

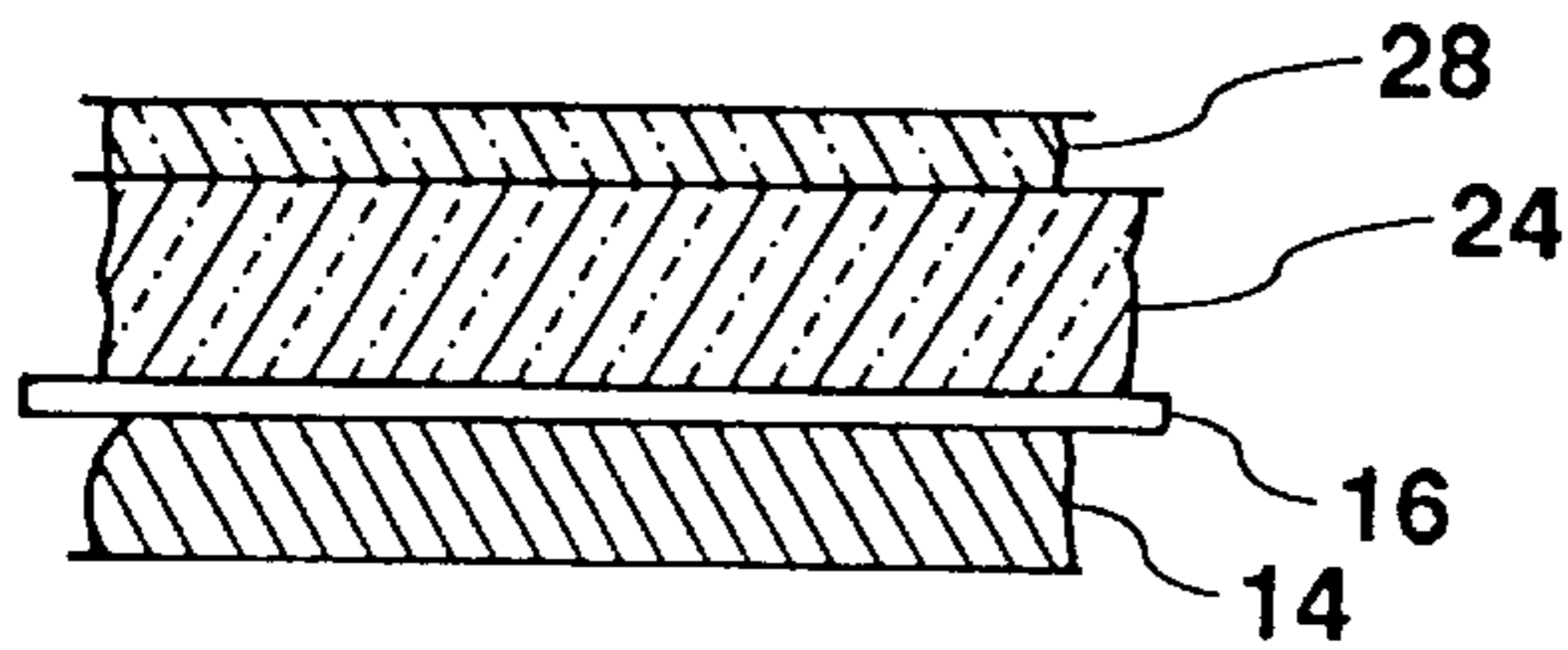


FIG 3

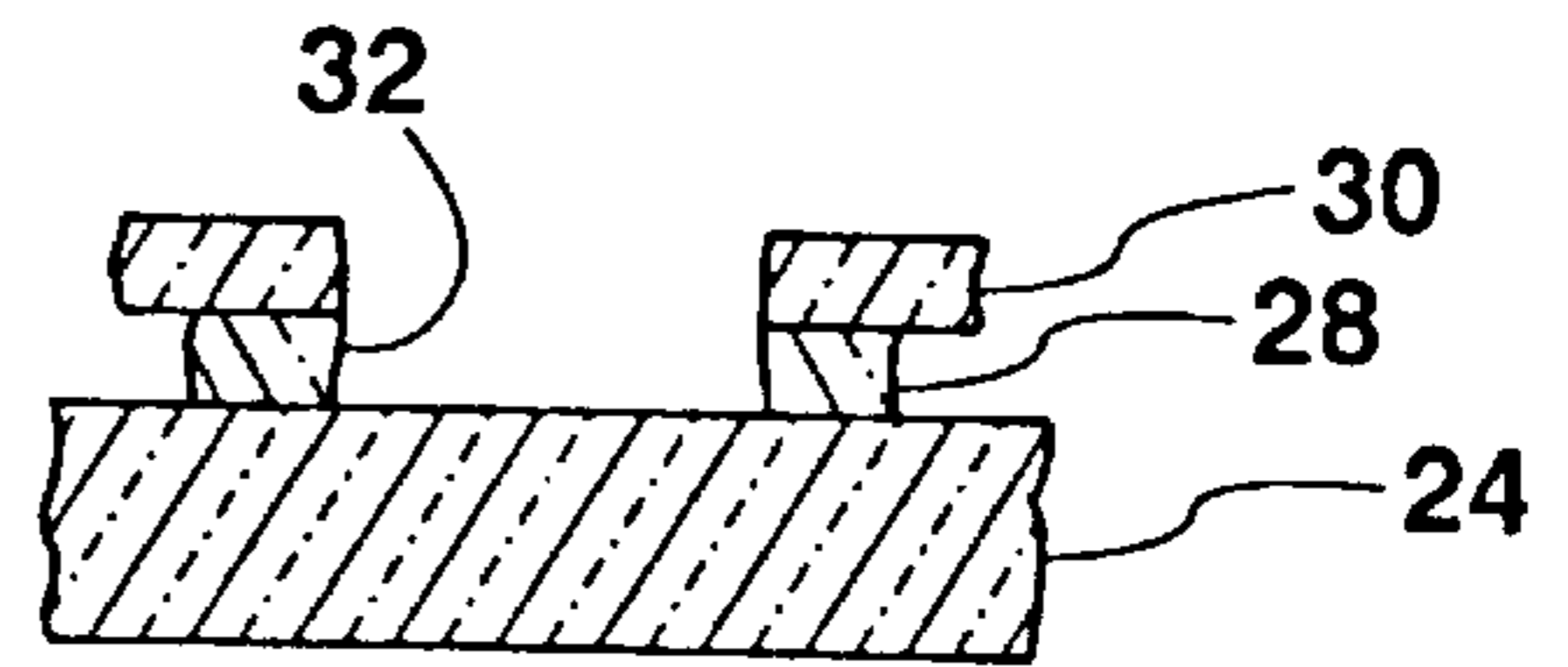


FIG 4

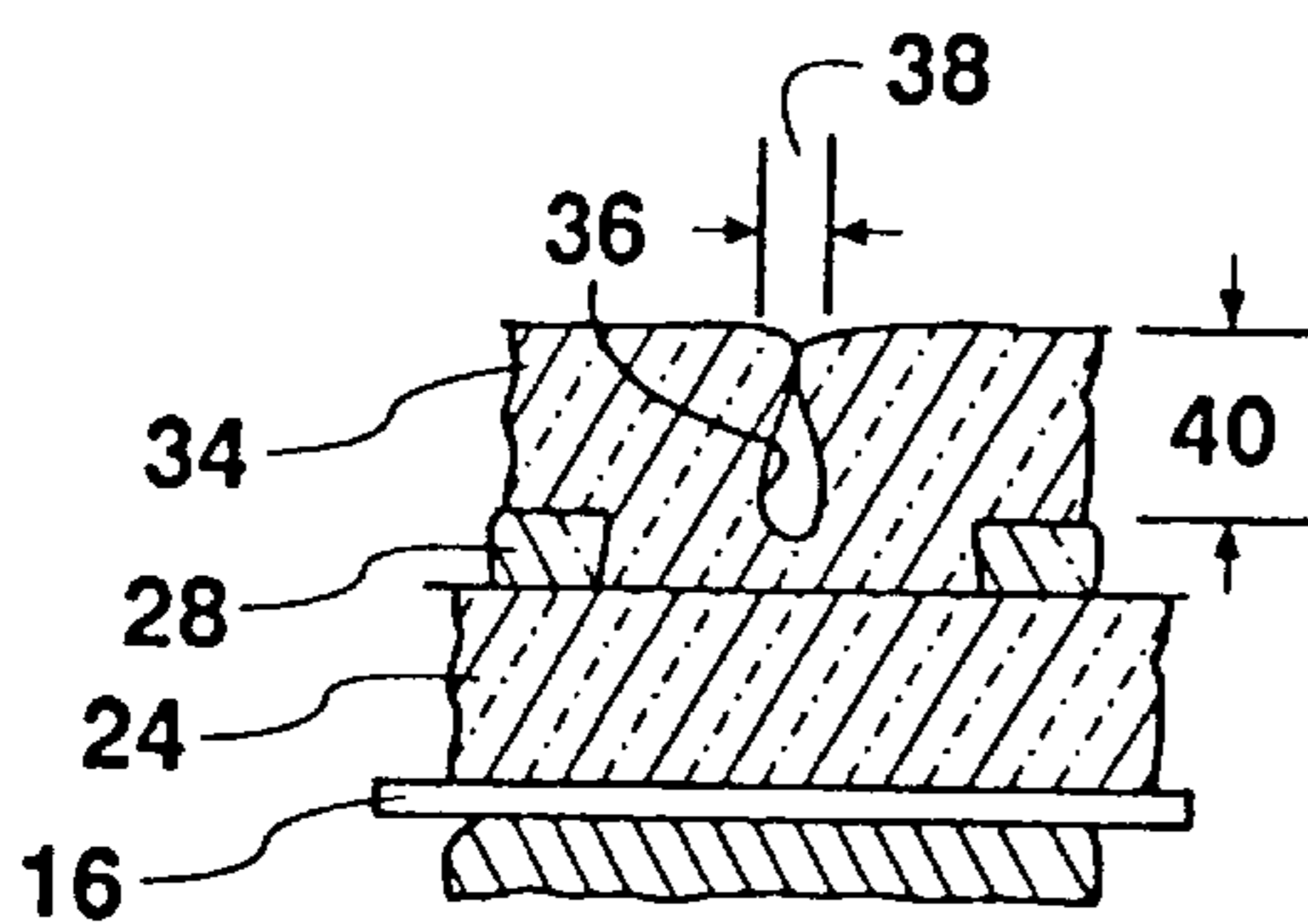


FIG 5

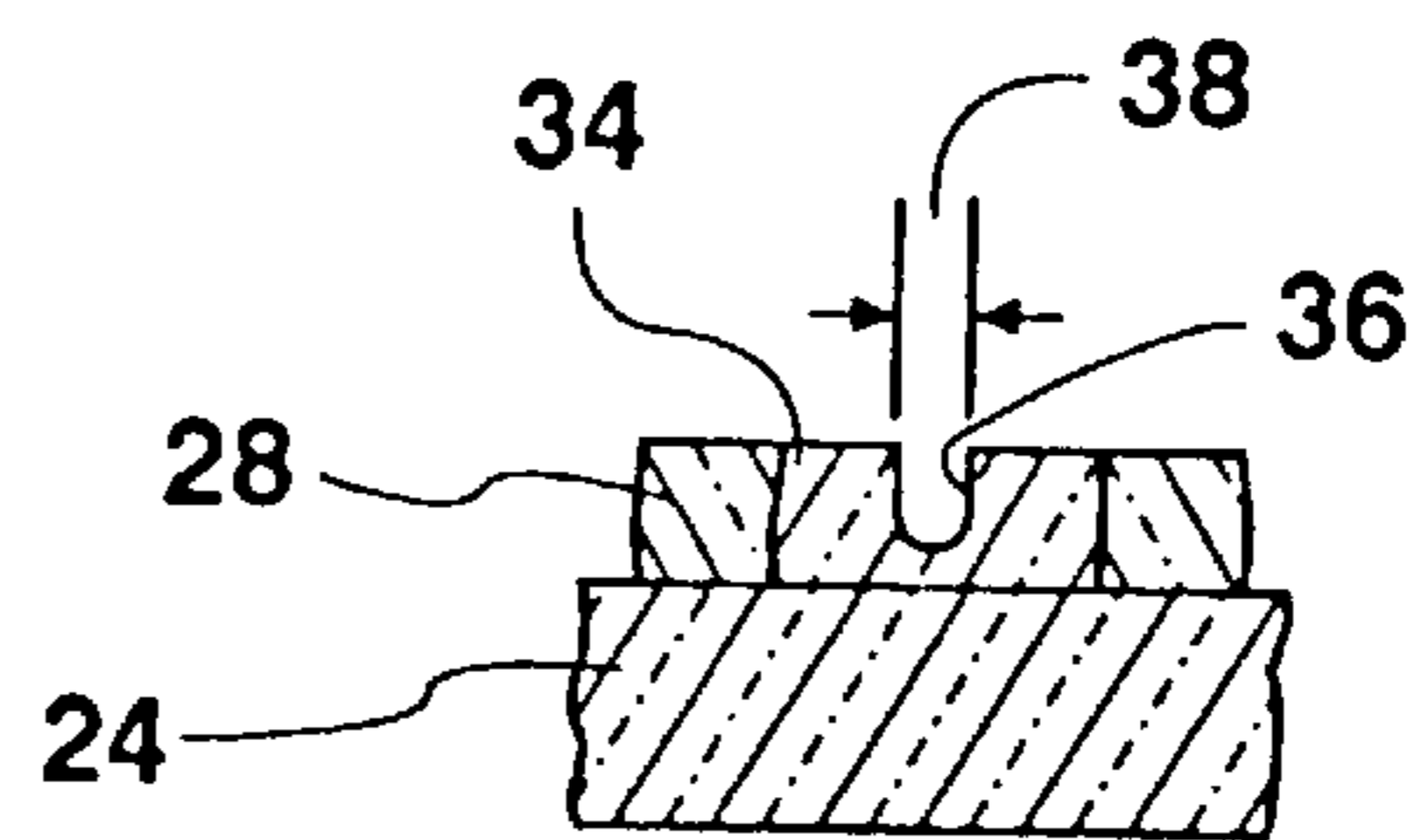


FIG 6

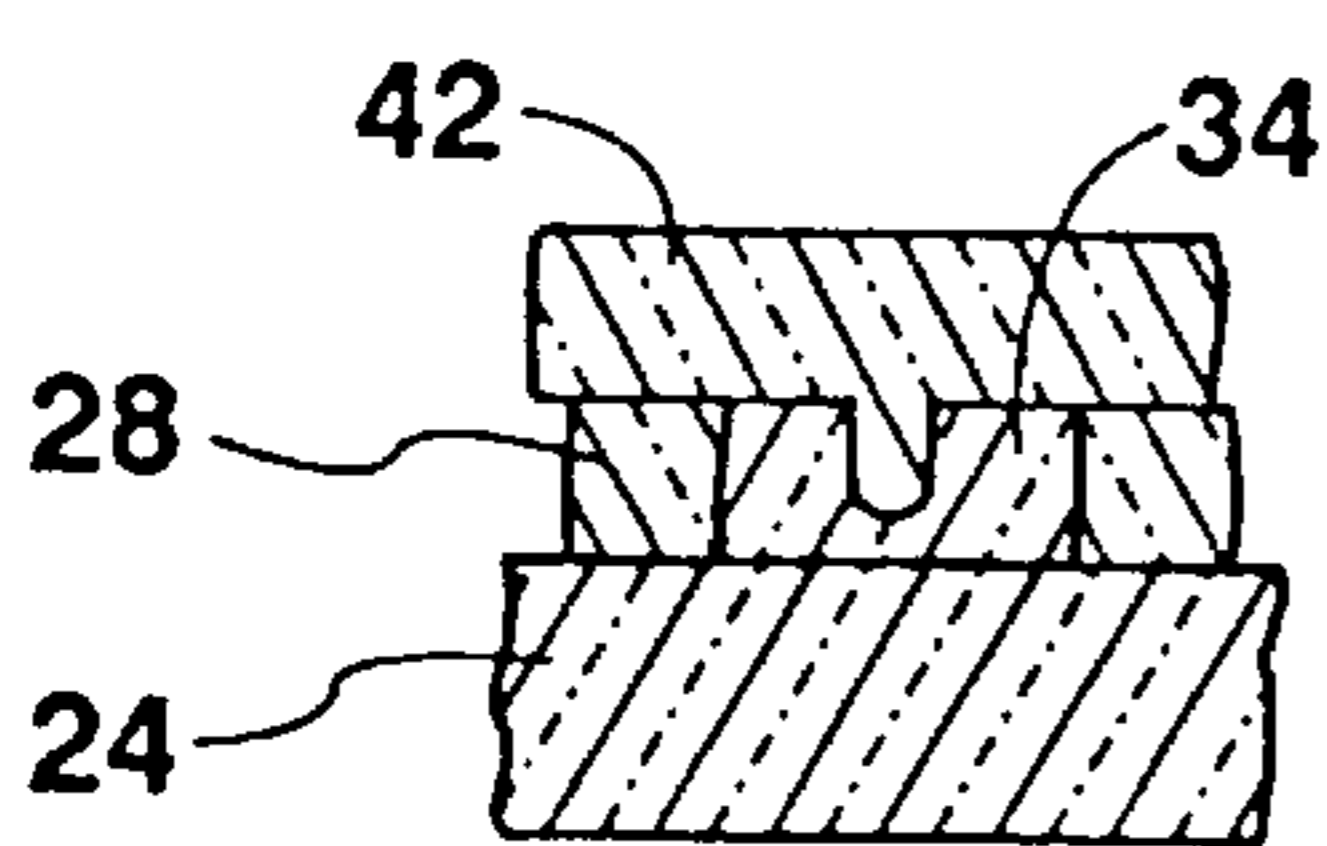


FIG 7

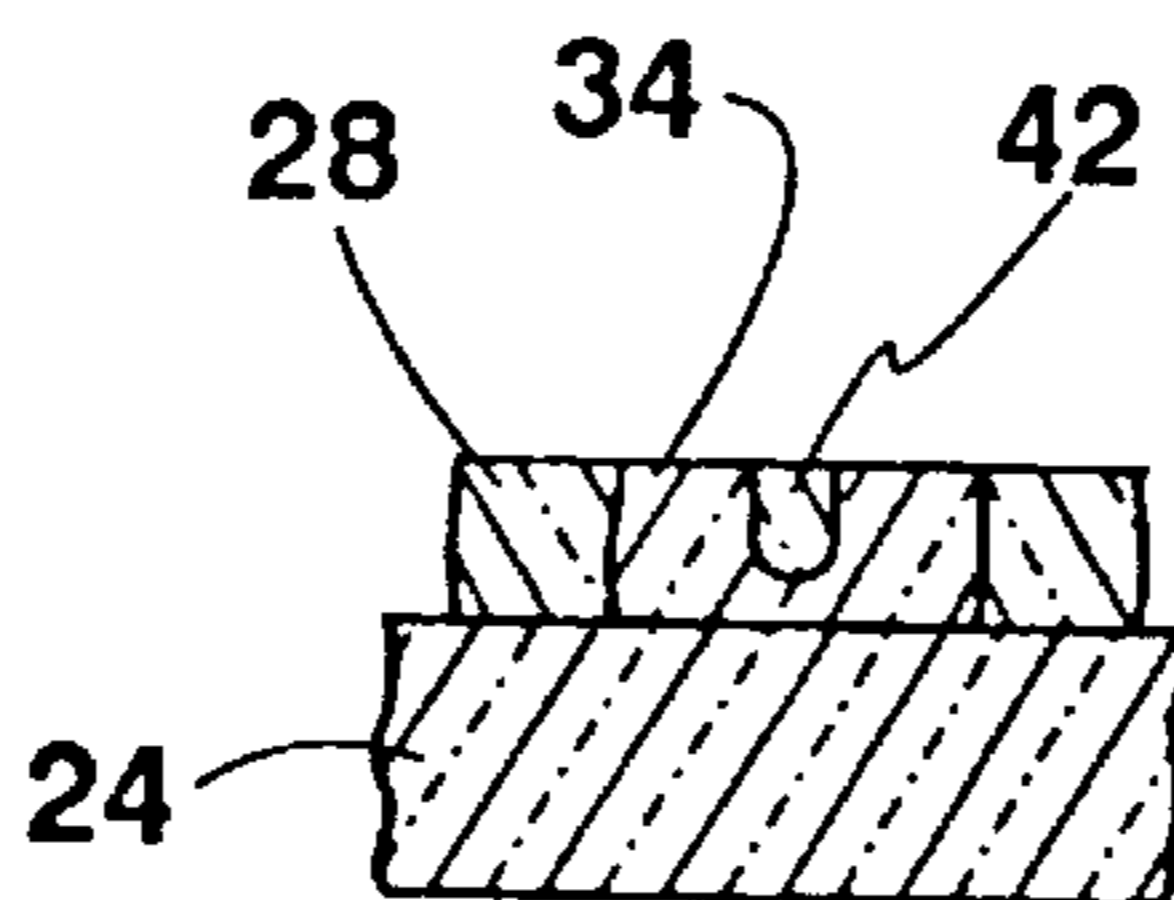


FIG 8

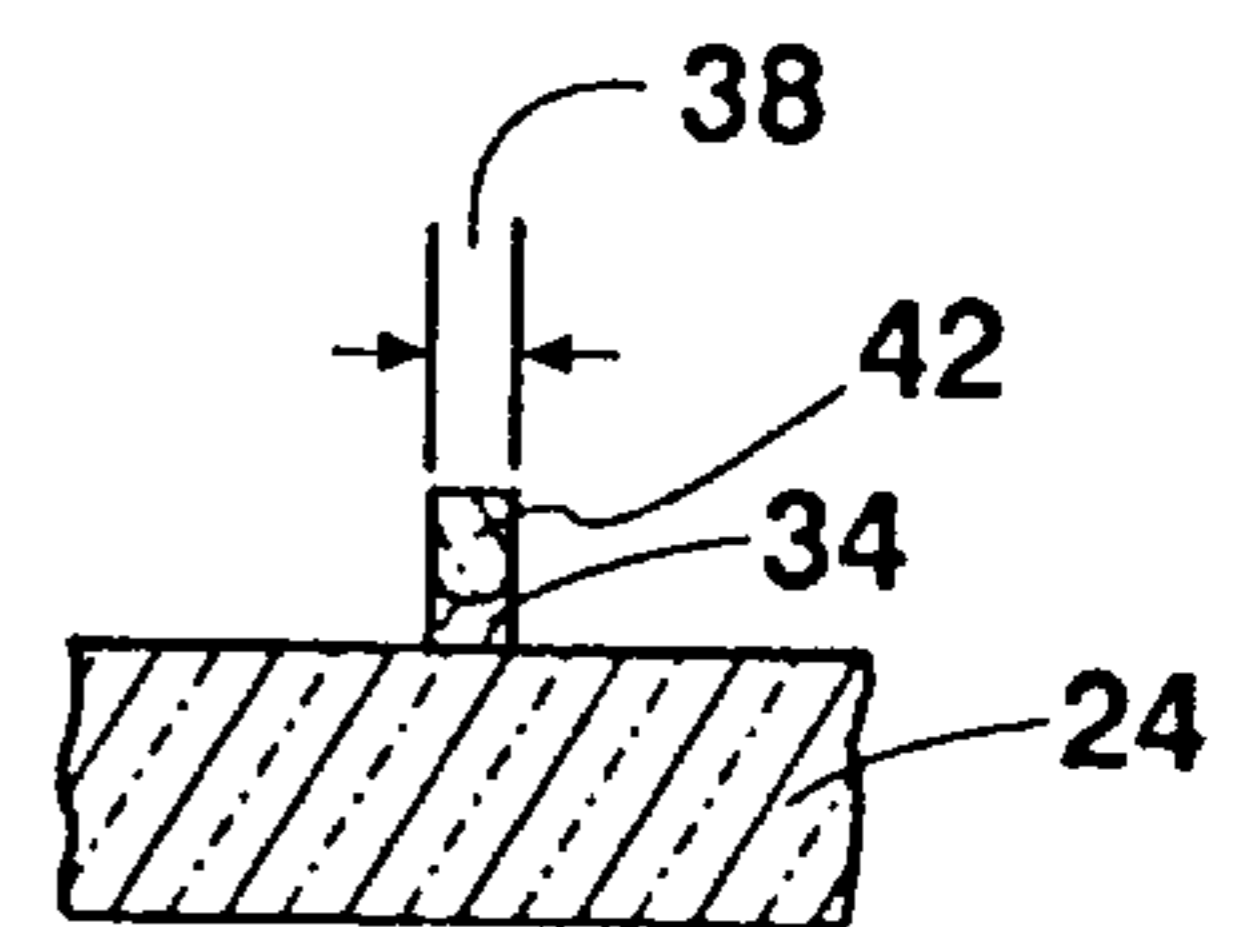


FIG 9

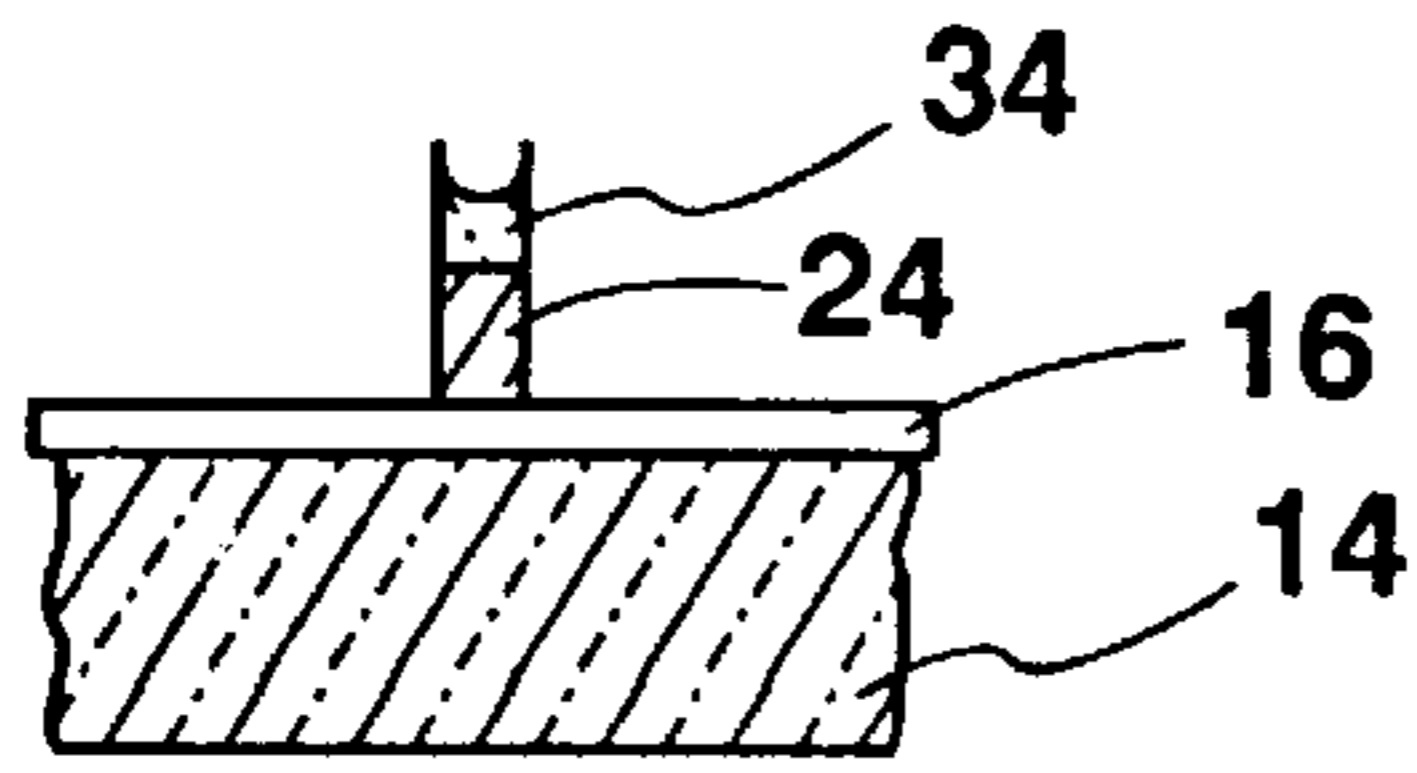


FIG 10

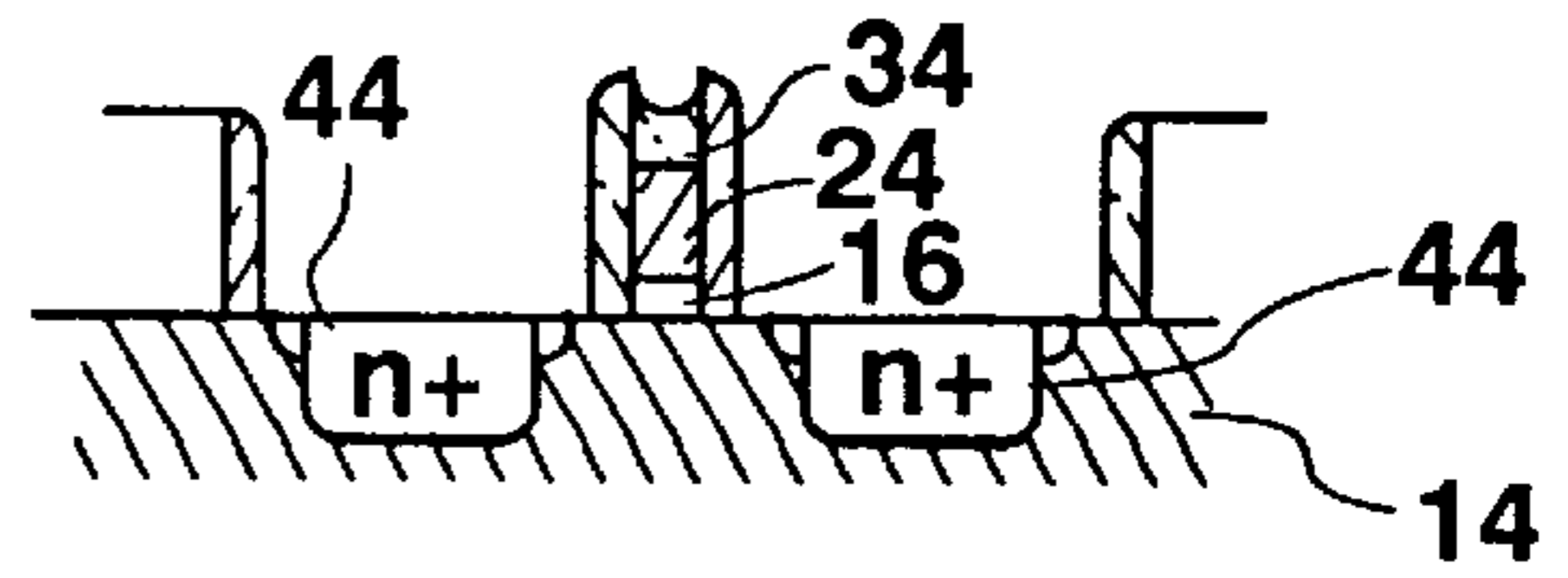


FIG 11

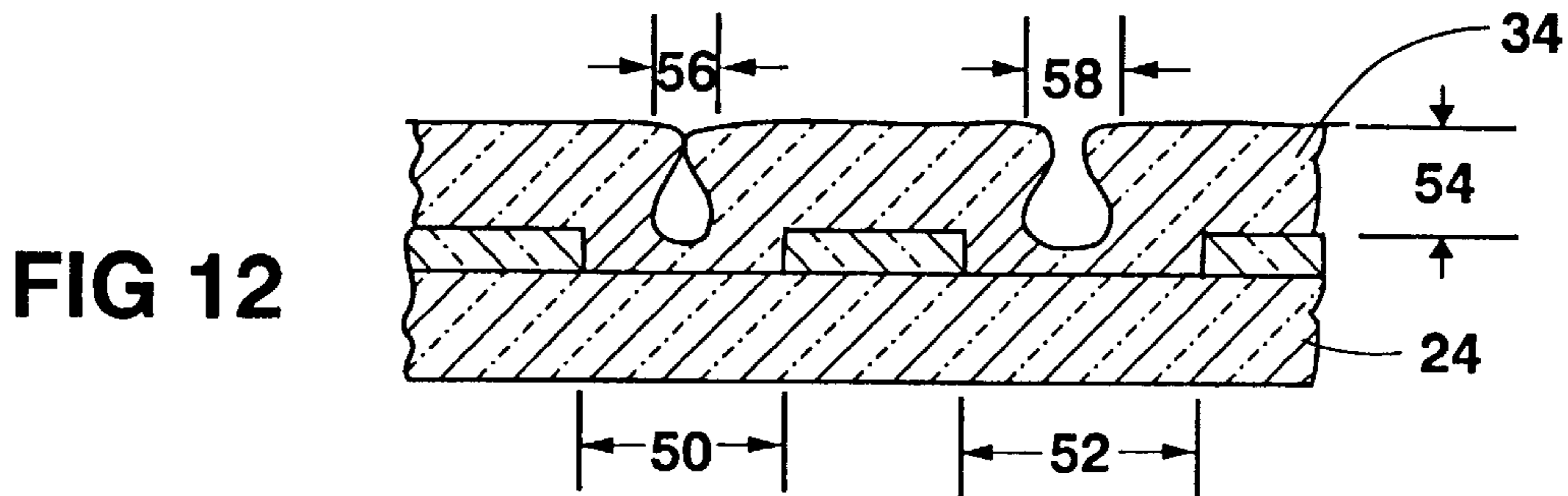


FIG 12

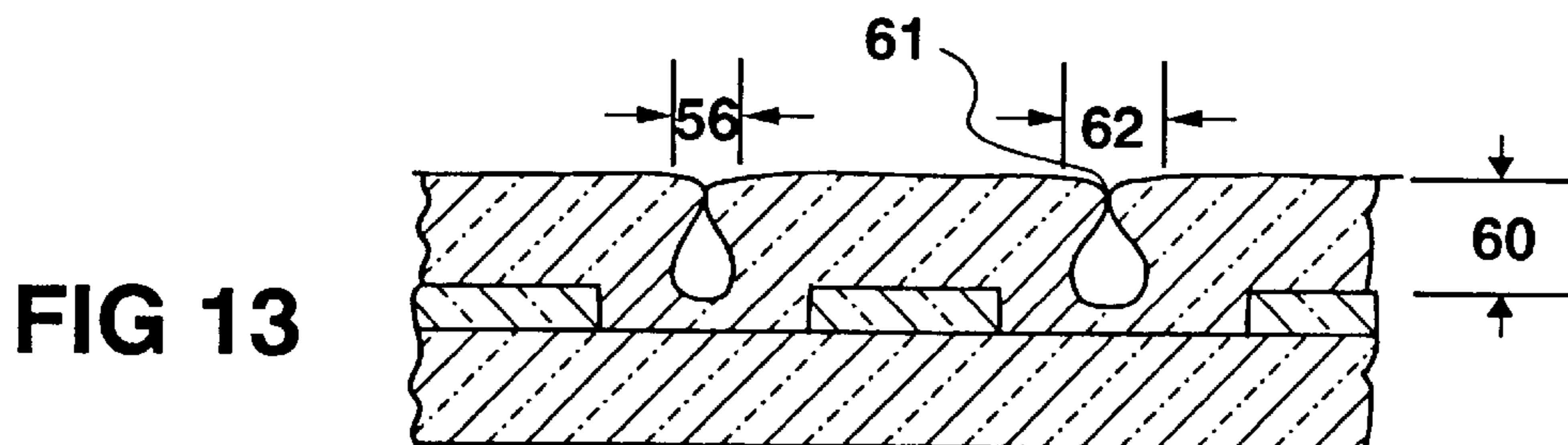


FIG 13

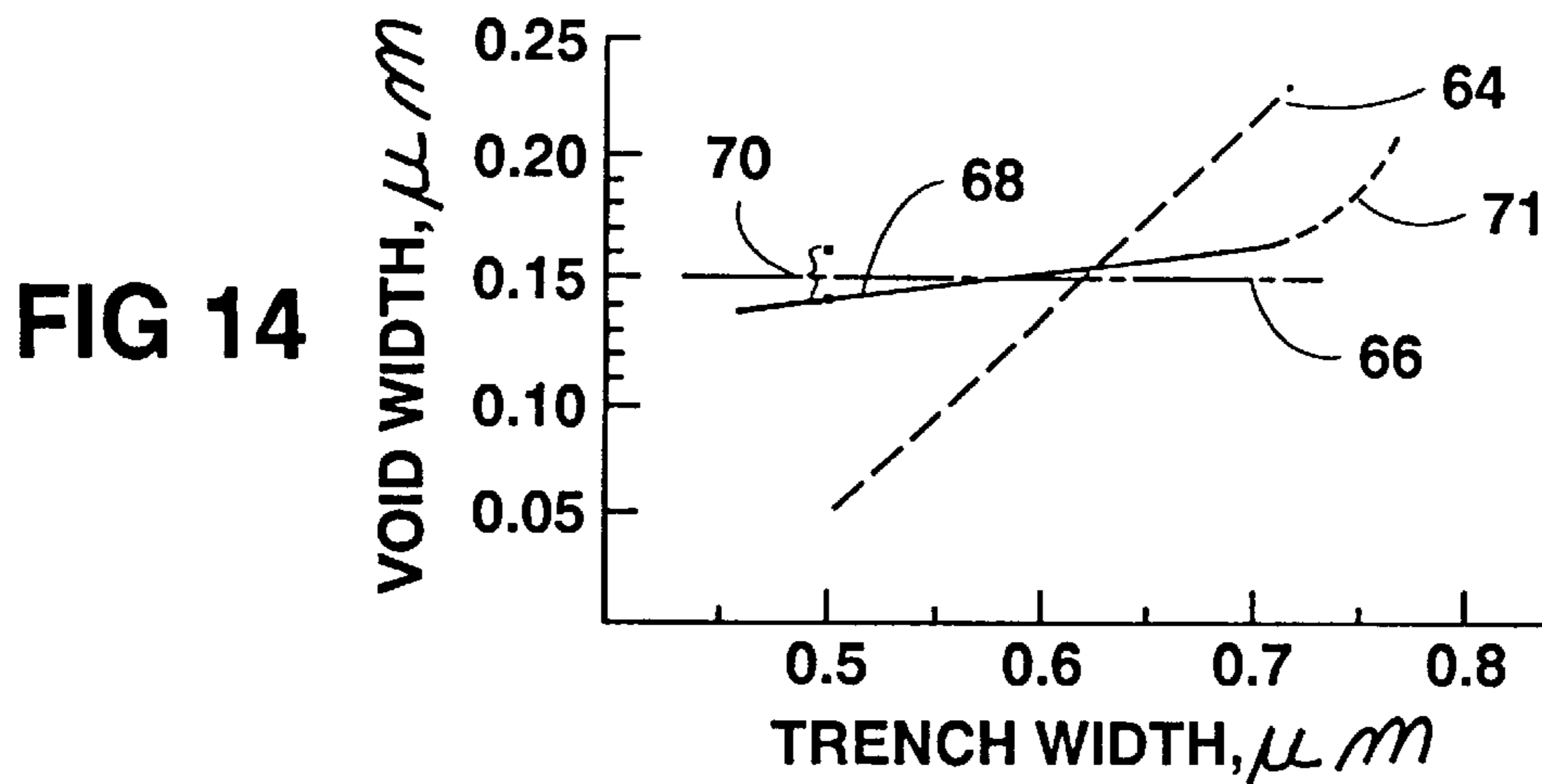


FIG 14

FIG 15

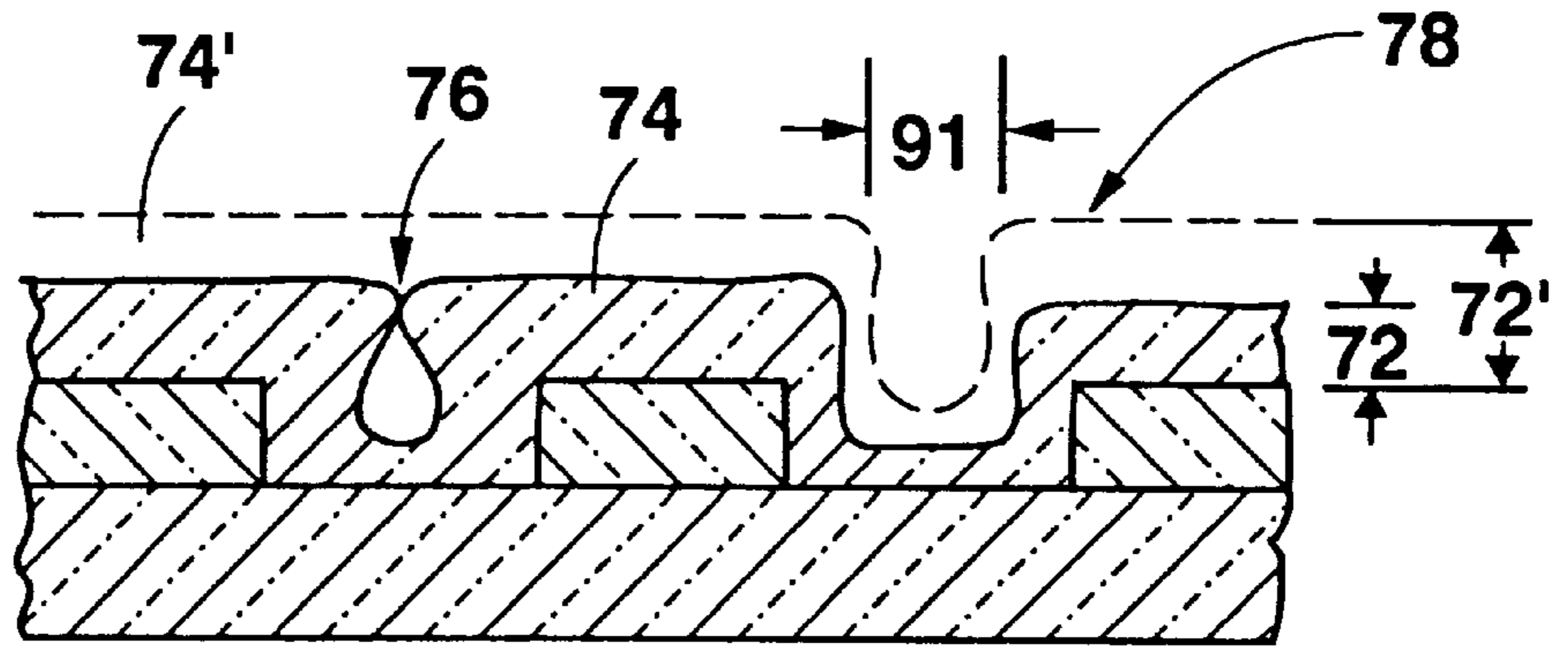


FIG 16

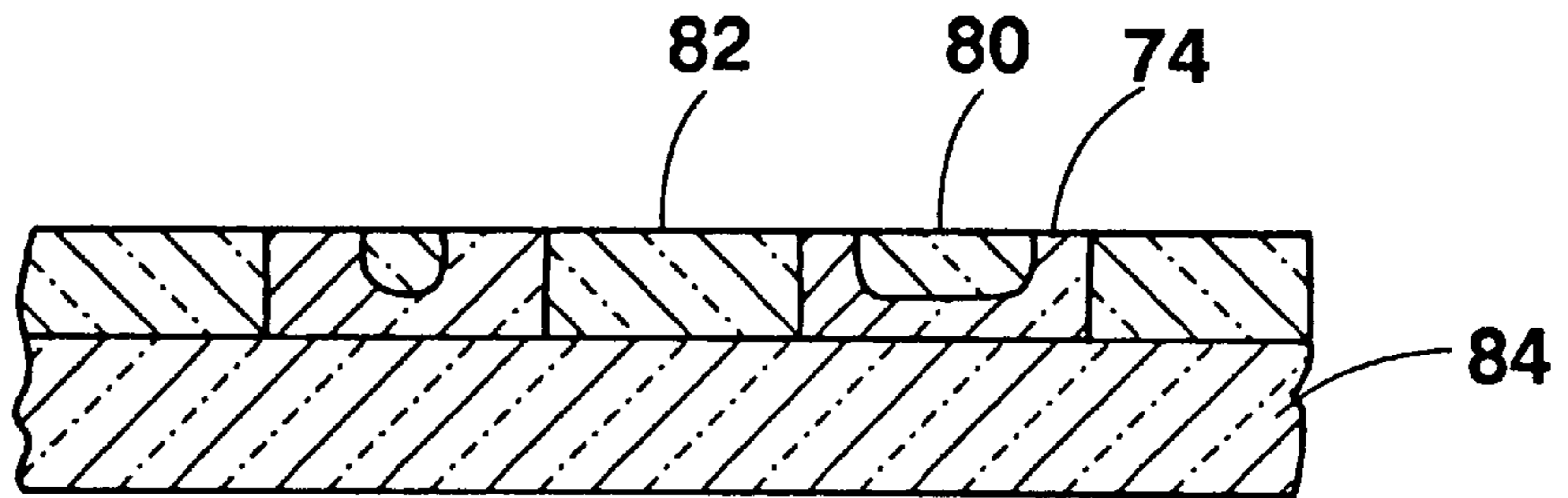
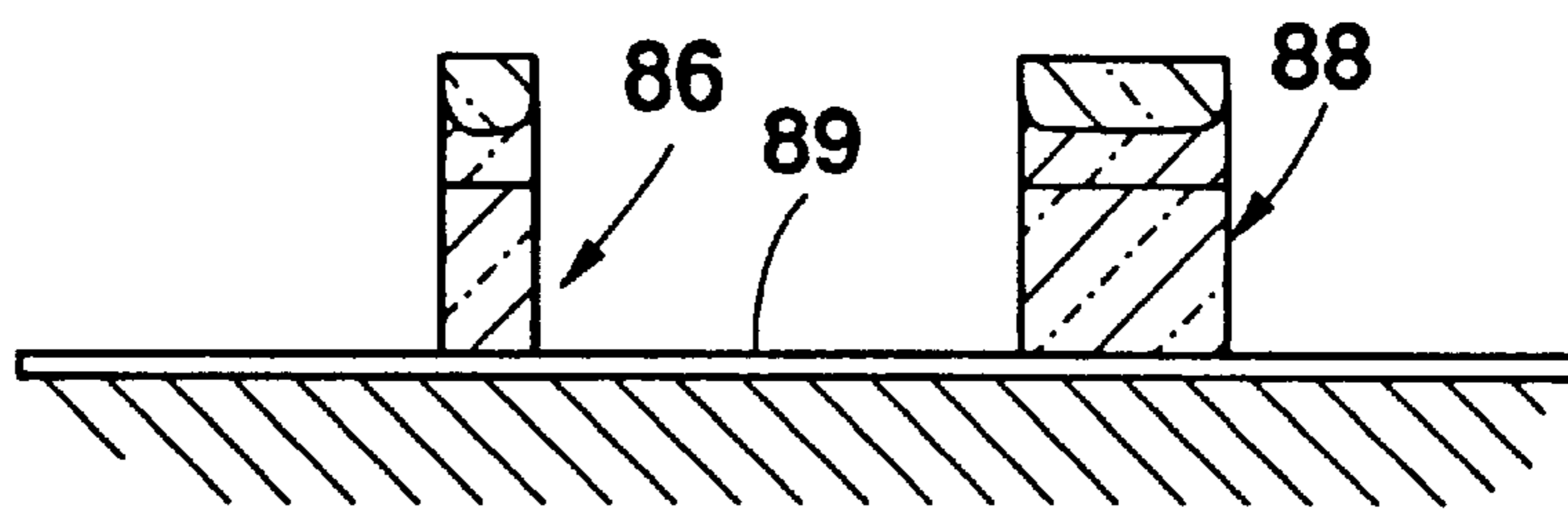
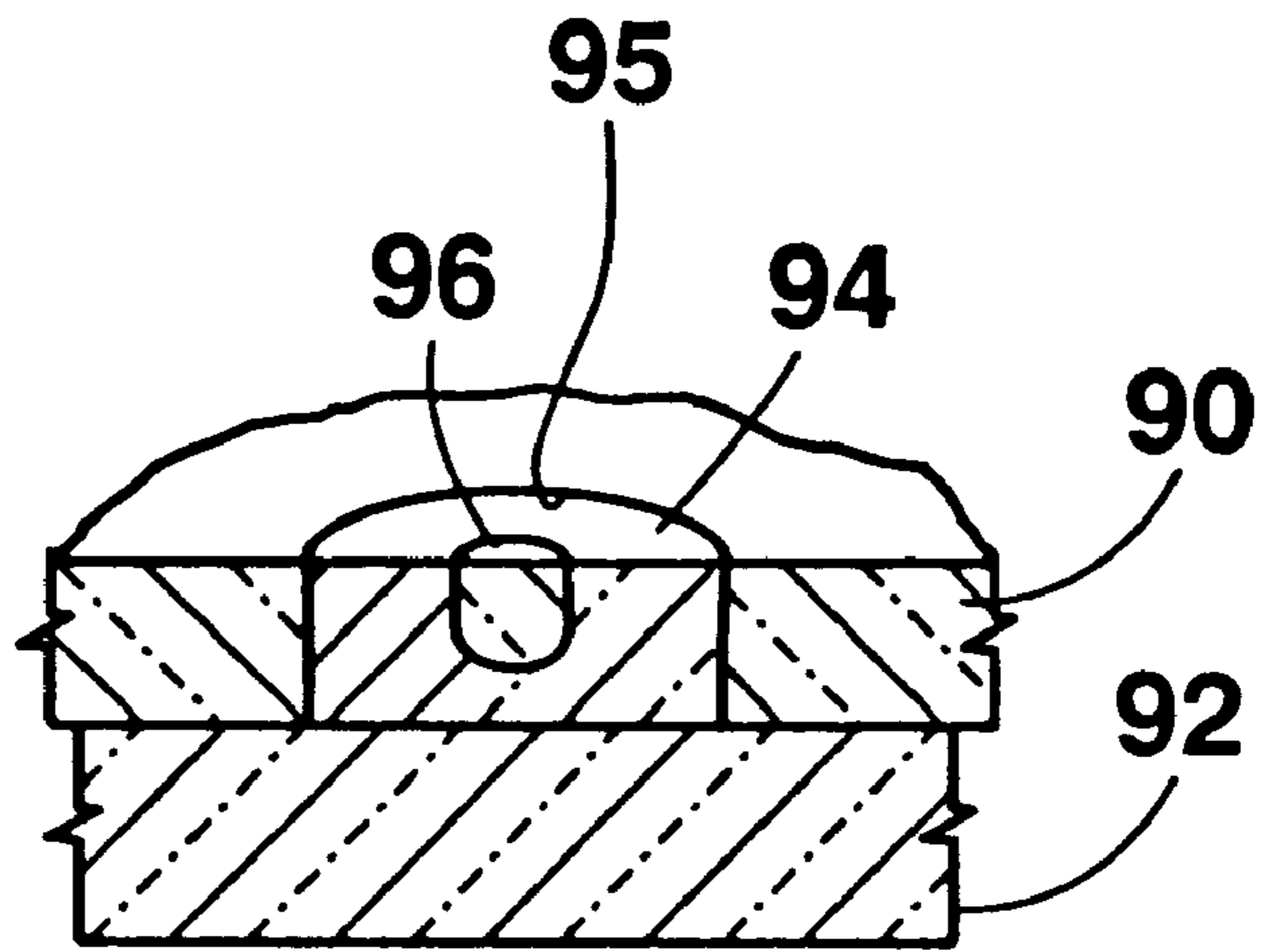


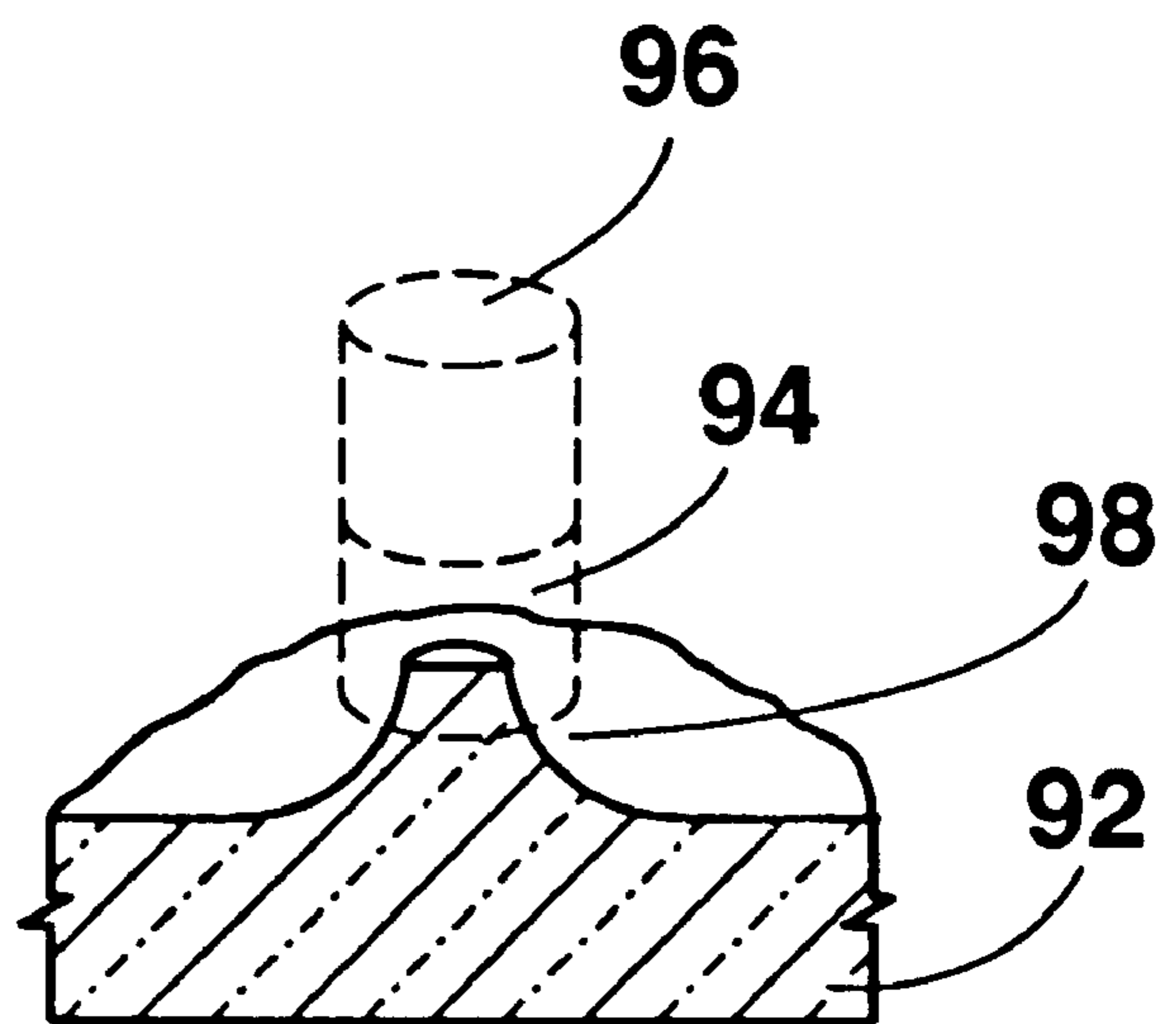
FIG 17



**FIG 18**



**FIG 19**



**METHOD FOR FABRICATION OF  
CLOSE-TOLERANCE LINES AND SHARP  
EMISSION TIPS ON A SEMICONDUCTOR  
WAFER**

**Matter enclosed in heavy brackets [ ] appears in the original patent but forms no part of this reissue specification; matter printed in italics indicates the additions made by reissue.**

FIELD OF THE INVENTION

The invention relates in general to a method for fabricating submicron lines on wafers and sharp tips for field effect device and, in particular, to the method for forming a close-tolerance line or sharp tip in a semiconductor wafer substrate or layer using a loose tolerance trench, or well.

BACKGROUND OF THE INVENTION

Often times in semiconductor wafer fabrication, it is desirable to fabricate a line having closer tolerances than photolithography or other line-forming methods. These close-tolerance lines are utilized for field effect devices and other integrated circuit devices produced on semiconductor wafers. In the past, it has been necessary to either purchase expensive precision fabrication equipment or relax the tolerances. Accordingly, it would be desirable to have a method for fabricating a close-tolerance line or sharp tip without requiring close-tolerance precise fabrication equipment. One example of use of this line would be for a narrow gate on a MOS FET device.

SUMMARY OF THE INVENTION

The present invention is a novel method for producing close-tolerance sharp tips or narrow lines in a semiconductor wafer substrate or layer where the fabrication equipment, i.e., photolithography apparatus, is only capable of producing a larger, looser tolerance line. The first step of the method is to fabricate a trench in a first layer over the substrate using the looser tolerance photolithography or other fabrication equipment available. The next step is to deposit a non-conformal material over the wider line and substrate, thereby forming a void with a uniform, close-tolerance width regardless of variations in the previously formed trench. Next, a chemical mechanical polish (CMP) process is performed to planarize and expose the close-tolerance width dimension void. An etch-resist conformal material is then deposited over the first layer and in the void. The conformal material is then planarized leaving material only in the void to form a mask of a predetermined close-tolerance width. The walls of the non-conformal material and the first layer are then etched away, leaving a ridge or wall under the mask of the same close-tolerance thickness as the void, disposed above the original wafer substrate in a position where a new line of close tolerance is to be formed at the predetermined desired position along the substrate.

This formed, two-layer ridge or wall then acts as a hard mask for subsequent patterning of the substrate by etching or other fabrication techniques. The ridges or lines formed in this manner can be in the range of 0.1 to 0.15  $\mu\text{m}$ .

In a second embodiment, the same process can be used to form a sharp, pointed tip such as that desired for high resolution field emission tips used in cold cathode emitters that are utilized in the field emitter display devices. In this case, the tip mask is formed as a cylindrical vertical pillar in lieu of a line or linear trench.

Other objects, advantages, and capabilities of the present invention will become more apparent as the description proceeds.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a perspective view of a submicron line formed by the present inventive method;

FIG. 2 is a perspective view of a sharp tip formed by the present method;

FIG. 3 is a partial side section view of an integrated circuit (IC) semiconductor die;

FIG. 4 is a partial side section view of an upper section the IC semiconductor die of FIG. 3 after etching;

FIG. 5 is a partial side section view of an IC semiconductor die of FIG. 4 after non-conformal layering;

FIG. 6 is a partial side section view of an IC semiconductor die of FIG. 5 after planarizing;

FIG. 7 is a partial side section view of an IC semiconductor die of FIG. 6 after conformal layering;

FIG. 8 is a partial side section view of an IC semiconductor die of FIG. 7 after a second planarizing of the conformal layer;

FIG. 9 is a partial side section view of an IC semiconductor die of FIG. 8 after a selective etching;

FIG. 10 is a partial side section view of an IC semiconductor die of FIG. 9 after a second selective etching;

FIG. 11 is a partial side section view of an IC semiconductor die of the final submicron line;

FIG. 12 is a partial side section view of an IC semiconductor die having a pair of trenches of differing widths filled with a non-conformal layer;

FIG. 13 is the partial side section view of an IC semiconductor die having a pair of trenches of differing widths of FIG. 12 now filled with a non-conformal layer of deeper depth;

FIG. 14 is a graph of void width as a function of trench width;

FIG. 15 is a partial side section view of an IC semiconductor die having a non-conformal layer over different width trenches;

FIG. 16 is a partial side section view of an IC semiconductor die having a non-conformal layer over different width trenches after planarization;

FIG. 17 is a partial side section view of an IC semiconductor die having different width lines;

FIG. 18 is a partial section perspective view of a sharp point "mask" process; and

FIG. 19 is a partial section perspective view of a completed sharp point.

DETAILED DESCRIPTION OF THE  
INVENTION

The final submicron line **10** fabricated by this inventive process can be seen in FIG. 1. This line which may be used as a gate in a final integrated circuit (IC) device and can have a width dimension of 0.1  $\mu\text{m}$  as at **12** which is significantly narrower than the width available by current photolithography methods. The line has been fabricated in substrate **14** and has a gate oxide layer **16** under the line **10**.

In a second embodiment, a sharp point **20** may be seen in FIG. 2 fabricated by the same basic process. A sharp point is needed in the fabrication of a field emitter device having a cold cathode (point) **20**, a control grid, and an anode (not shown) on a substrate **22**. The process for forming the point **20** is similar to the submicron line process except for the shape, i.e., a circular pyramid **20** in lieu of a line **10** (FIG. 1).

The process for submicron line formation **10** will be described by referring to FIGS. **3–11**. FIG. **3** indicates the typical beginning steps in IC semiconductor wafer. The substrate **14** has a typical gate oxide layer **16** formed over substrate **14** and a typical gate polysilicon layer **24** deposited over the oxide **16**. A mask oxide layer **28** is deposited over the gate polysilicon layer **24**. FIG. **4** shows the results of the photolithography method of forming a trench through a photoresist layer **30** and the mask oxide layer **28** by an etching process. After etching, the photoresist layer **30** is removed by a stripping process. The line or trench **32** is then filled by depositing a non-conformal material **34** as in FIG. **5** which in this inventive process forms a tear-drop shaped void or gap **36** at the center of line **32**. A good material for this layer would be plasma silicon oxide ( $\text{SiO}_2$ ) or plasma silicon nitride ( $\text{Si}_3\text{N}_4$ ). Plasma oxide will be used in the described process flow. The depth of layer **34** is controlled and is dependent on the width and depth of line **32**. As shown, a typical void width is about  $0.1 \mu\text{m}$  as at **38** when the depth of the non-conformal layer is  $0.45 \mu\text{m}$  as at **40**.

After planarizing the non-conformal material **34** by a chemical mechanical polish, the surface and exposed void **36** appears as in FIG. **6**. A key aspect of this invention is the ability to form a void of consistent width **38** without being affected by minor variations in the width of gap **32** which is due to the physical limitations of the photolithography and etch processes.

Referring now to FIG. **7**, a conformal mask material **42** is deposited and may consist of any conformal material capable of having a differing plasma etch rate than layer **34**. For the process flow shown, polysilicon is deposited by a low pressure chemical vapor deposition (LPCVD) process and is representative of such conformal material.

A second chemical mechanical polishing is performed to remove all the conformal material **42** except that within void **36**, as illustrated in FIG. **8**. An anisotropic oxide etch simultaneously etches both the plasma oxide **34** and masking oxide **28** down to gate polysilicon layer **24**, as in FIG. **9**. Next, a plasma polysilicon etch can be done to pattern the underlying oxide **16** and gate polysilicon **24** to form the submicron ( $0.1 \mu\text{m}$ ) line as illustrated in FIG. **10**. Also, note that the conformal polysilicon layer **42** is simultaneously etched away in this polysilicon etch step. FIG. **11** illustrates the submicron gate material **24** and gate oxide **16** over substrate **14** after typical ion implantation at **44**. The remaining steps in the process are dependent on the type of device being fabricated.

Referring now to FIGS. **12** and **13**, the capability to form lines of consistent close-tolerance width in spite of variations in trench width **50,52** is demonstrated. Trench lines **50** and **52** have a typical width dimension of  $0.4 \mu\text{m}$  and  $0.6 \mu\text{m}$ , respectively, and the deposition of non-conformal layer **34** to a depth of about  $0.3 \mu\text{m}$  is shown at **54**. Void width at **56** is shown about  $0.1 \mu\text{m}$  while void **58** at this point is about  $0.2 \mu\text{m}$ . FIG. **13** shows the effect of continuing the deposition of layer **34** to about  $0.45 \mu\text{m}$  as at **60**. This deposition to a depth of  $0.45 \mu\text{m}$  at **60** has resulted in closing the void at the top section **61** and narrowing the void at **58** to a new void width of  $0.1 \mu\text{m}$  at **62**, thereby matching the void width **56**.

The graph of FIG. **14** is used to illustrate the variation of void width as a function of trench width. Using a conformal material would result in linear relationship at **64**. The ideal response would be a flat line as at **66**, and a desired response or relationship is shown at **68** which indicates about a  $0.02 \mu\text{m}$  change in void width for a  $0.2 \mu\text{m}$  change in trench width as at **70**. For trench widths over  $0.7 \mu\text{m}$ , the line **68** would curve upward so as to be parallel to line **64** as at **71** (FIG. **14**).

Referring to FIGS. **15–17**, it is also demonstrated that it is also possible to purposely fabricate wide lines and narrow lines simultaneously by controlling the non-conformal layer depth **72**. In this instance, the non-conformal layer **74** is above two significantly different width trenches **76** and **78**. When these trenches have the conformal mask material **80** deposited and then planarized down to the polysilicon layer **82**, the cross-section appears as at FIG. **16**. A final gate material **84** cross-section shown in FIG. **17** would have a narrow gate line **86** and wider gate line **88** after etching down to gate oxide **89**. It is noted that for the wider trench widths, the final mask width can be controlled by careful control of the non-conformal mask material depths as at **72'** (FIG. **15**), i.e., the deeper the mask depth deposited, the narrower the final gap as at **91** (FIG. **15**).

The cross-section perspective view of FIG. **18** discloses the fabrication process to make a sharp point for a cold cathode or similar device as shown in FIG. **19**. In this case, we have polysilicon layer **90** over the substrate **92** and a non-conformal circular plug **94** in a well **95** in lieu of a trench or line (FIGS. **6–8**) and the hard mask TEOS **96** or other material sets within well **95** surrounded by the plug **94**. Isotropic etching of the substrate **92** and mask and plug removal would expose the cone-shaped sharp point as at **98** (FIG. **19**) of a very small diameter, on the order of  $0.1 \mu\text{m}$ . A cylindrical pillar could also be formed by use of an anisotropic etch process.

It is also possible to fabricate circular gates and anodes surrounding the sharp tip **98** by a similar process.

While preferred embodiments of the invention have been disclosed, various modes of carrying out the principles disclosed herein are contemplated as being within the scope of the following claims. Therefore, it is understood that the scope of the invention is not to be limited except as otherwise set forth in the claims.

What is claimed is:

1. A method for fabricating close-tolerance submicron lines on a semiconductor wafer having a gate oxide layer over a substrate and a gate polysilicon layer over the gate oxide, comprising the steps of:

- a. depositing a first layer on top of the gate polysilicon layer;
- b. forming a loose-tolerance trench in the first layer having a width of less than 1 micrometer ( $\mu\text{m}$ );
- c. depositing a non-conformal material to a predetermined thickness of between  $0.3$  and  $0.45 \mu\text{m}$  over the first layer thereby forming a teardrop-shaped void in the trench, said teardrop-shaped void having a narrow, close-tolerance uniform width dimension;
- d. chemically, mechanically polishing (CMP) the non-conformal material down to a top surface of the first layer, thereby exposing the void;
- e. depositing a conformal mask material over the first layer and void;
- f. CMP polishing and removing the conformal mask material down to the first layer, thereby leaving only the narrow void filled with conformal mask material;
- g. anisotropically etching by a photolithography process, the first layer and non-conformal material thereby forming the submicron line below the conformal mask material.

2. The method of claim **1** wherein the loose-tolerance trench is between  $0.40 \mu\text{m}$  and  $0.7 \mu\text{m}$ .

3. The method of claim **1** wherein the first layer is a mask oxide.

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4. The method of claim 1 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.

5. The method of claim 1 wherein the conformal mask material is polysilicon.

6. The method of claim 2 wherein the width of the submicron line is less than  $0.15\ \mu\text{m}$ .

7. A method for fabricating close-tolerance, sharp emission tip on a semiconductor wafer having a gate oxide layer over a substrate and a gate polysilicon layer over the gate oxide, comprising the steps of:

- a. depositing a first layer on top of the gate polysilicon layer;
- b. forming a loose-tolerance trench in the first layer having a diameter of less than 1 micrometer ( $\mu\text{m}$ );
- c. depositing a non-conformal material to a predetermined thickness of between  $0.3$  and  $0.45\ \mu\text{m}$  over the first layer thereby forming a teardrop-shaped void in the trench, said teardrop-shaped void having a narrow, close-tolerance, uniform diameter;
- d. chemically, mechanically polishing (CMP) the non-conformal material down to a top surface of the first layer, thereby exposing the void;
- e. depositing a conformal mask material over the first layer and void;
- f. CMP polishing and removing the conformal mask material down to the first layer, thereby leaving only the void filled with conformal mask material;
- g. isotropically etching by a photolithography process the first layer and non-conformal material thereby forming the sharp emission tip below the conformal mask material having a lesser diameter than the loose-tolerance well.

8. The method of claim 7 wherein the loose-tolerance well is between  $0.40\ \mu\text{m}$  and  $0.7\ \mu\text{m}$  diameter.

9. The method of claim 7 wherein the first layer is a mask oxide.

10. The method of claim 7 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.

11. The method of claim 7 wherein the conformal mask material is polysilicon.

12. The method of claim 8 wherein the diameter of the sharp emission tip is less than  $0.15\ \mu\text{m}$ .

13. A method for fabricating close-tolerance mask on a semiconductor wafer having a gate oxide layer over a substrate and a gate polysilicon layer over the gate oxide, comprising the steps of:

- a. depositing a first layer on top of the gate polysilicon layer;
- b. forming a loose-tolerance trench in the first layer having a width of less than 1 micrometer ( $\mu\text{m}$ );
- c. depositing a non-conformal material to a predetermined thickness of between  $0.3$  and  $0.45\ \mu\text{m}$  over the first layer thereby forming a teardrop-shaped void in the trench, said teardrop-shaped void having a narrow, close-tolerance uniform width dimension;
- d. chemically, mechanically polishing (CMP) the non-conformal material down to a top surface of the first layer, thereby exposing the void;
- e. depositing a conformal mask material over the first layer and void; and then
- f. CMP polishing and removing the conformal mask material down to the first layer, thereby leaving only the narrow void filled with conformal mask material.

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14. The method of claim 13 wherein the loose-tolerance trench is between  $0.40\ \mu\text{m}$  and  $0.7\ \mu\text{m}$ .

15. The method of claim 13 wherein the first layer is a mask oxide.

16. The method of claim 13 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.

17. The method of claim 13 wherein the conformal mask material is polysilicon.

18. The method of claim 14 wherein the width of the mask is less than  $0.15\ \mu\text{m}$ .

19. A method for fabricating close-tolerance, circular mask on a semiconductor wafer having a gate oxide layer over a substrate and a gate polysilicon layer over the gate oxide, comprising the steps of:

- a. depositing a first layer on top of the gate polysilicon layer;
- b. forming a loose-tolerance well in the first layer having a width of less than 1 micrometer ( $\mu\text{m}$ );
- c. depositing a non-conformal material to a predetermined thickness of between  $0.3$  and  $0.45\ \mu\text{m}$  over the first layer thereby forming a teardrop-shaped void in the well, said teardrop-shaped void having a narrow, close-tolerance, uniform diameter;
- d. chemically, mechanically polishing (CMP) the non-conformal material down to a top surface of the first layer, thereby exposing the void;
- e. depositing a conformal mask material over the first layer and void; and then
- f. CMP polishing and removing the conformal mask material down to the first layer, thereby leaving only the void filled with conformal mask material.

20. The method of claim 19 wherein the loose-tolerance well is between  $0.40\ \mu\text{m}$  and  $0.7\ \mu\text{m}$  diameter.

21. The method of claim 19 wherein the first layer is a mask oxide.

22. The method of claim 19 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.

23. The method of claim 19 wherein the conformal mask material is polysilicon.

24. A method for fabricating at least one submicron line on a semiconductor substrate having an oxide layer over the semiconductor substrate and a polysilicon layer over the oxide layer, comprising:

- depositing a first layer on top of the polysilicon layer;
- forming a trench in the first layer;
- depositing a non-conformal material over the first layer to form a void in the trench;
- removing the non-conformal material down to a top surface of the first layer to expose the void;
- depositing a conformal mask material over the first layer and void;
- removing the conformal mask material above the first layer; and
- etching the first layer and non-conformal material.

25. The method of claim 24 wherein the trench includes a width of less than  $1\ \mu\text{m}$ .

26. The method of claim 24 wherein the trench is between  $0.40\ \mu\text{m}$  and  $0.7\ \mu\text{m}$  in width.

27. The method of claim 24 wherein the first layer is a mask oxide.

28. The method of claim 24 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.



29. The method of claim 24 wherein depositing the non-conformal material includes deposition to a thickness of between 0.3 and 0.45  $\mu\text{m}$ .

30. The method of claim 24 wherein the conformal mask material is polysilicon.

31. The method of claim 24 wherein the submicron line is less than 0.15  $\mu\text{m}$  in width.

32. The method of claim 24 wherein the void includes a tear-drop shaped cross section.

33. The method of claim 24 wherein removing the non-conformal mask material down to the top surface of the first layer includes chemical mechanical polishing.

34. The method of claim 24 wherein removing the conformal mask material above the first layer includes chemical mechanical polishing.

35. The method of claim 24 wherein etching the first layer and non-conformal material includes an anisotropic etch.

36. A method for fabricating at least one sharp emission tip on a semiconductor substrate having an oxide layer over the semiconductor substrate and a polysilicon layer over the oxide layer, comprising:

depositing a first layer on top of the polysilicon layer;

forming a well in the first layer;

depositing a non-conformal material over the first layer to form a void in the well;

removing the non-conformal material down to a top surface of the first layer to expose the void;

depositing a conformal mask material over the first layer and void;

removing the conformal mask material above the first layer; and

etching the first layer and non-conformal material.

37. The method of claim 36 wherein the well includes a diameter of less than 1  $\mu\text{m}$ .

38. The method of claim 36 wherein the well is between 0.40  $\mu\text{m}$  and 0.7  $\mu\text{m}$  in diameter.

39. The method of claim 36 wherein the first layer is a mask oxide.

40. The method of claim 36 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.

41. The method of claim 36 wherein depositing the non-conformal material includes deposition to a thickness of between 0.3 and 0.45  $\mu\text{m}$ .

42. The method of claim 36 wherein the conformal mask material is polysilicon.

43. The method of claim 36 wherein the sharp emission tip is less than 0.15  $\mu\text{m}$  in diameter.

44. The method of claim 36 wherein the void includes a tear-drop shape.

45. The method of claim 36 wherein removing the non-conformal mask material down to a top surface of the first layer includes chemical mechanical polishing.

46. The method of claim 36 wherein removing the conformal mask material above the first layer includes chemical mechanical polishing.

47. The method of claim 36 wherein etching the first layer and non-conformal material includes an anisotropic etch.

48. The method of claim 36 wherein etching the first layer and non-conformal material includes an isotropic etch.

49. A method for fabricating a mask on a semiconductor substrate having an oxide layer over the semiconductor substrate and a polysilicon layer over the oxide layer, comprising:

depositing a first layer on top on the polysilicon layer;

forming an opening in the first layer;

depositing a non-conformal material over the first layer to form a void in the opening;

removing the non-conformal material down to a top surface of the first layer to expose the void;

5 depositing a conformal mask material over the first layer and void; and

removing the conformal mask material above the first layer.

10 50. The method of claim 49 wherein the first layer is a mask oxide.

51. The method of claim 49 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.

15 52. The method of claim 49 wherein depositing the non-conformal material includes deposition to a thickness of between 0.3 and 0.45  $\mu\text{m}$ .

53. The method of claim 49 wherein the conformal mask material is polysilicon.

20 54. The method of claim 49 wherein the opening includes a trench.

55. The method of claim 54 wherein the trench is less than 1  $\mu\text{m}$  in width.

25 56. The method of claim 54 wherein the trench is between 0.40  $\mu\text{m}$  and 0.7  $\mu\text{m}$  in width.

57. The method of claim 54 wherein the mask is less than 0.15  $\mu\text{m}$  in width.

58. The method of claim 49 wherein the opening includes a well.

30 59. The method of claim 58 wherein the well is less than 1  $\mu\text{m}$  in diameter.

60. The method of claim 58 wherein the well is between 0.40  $\mu\text{m}$  and 0.7  $\mu\text{m}$  in diameter.

35 61. The method of claim 58 wherein the mask is less than 0.15  $\mu\text{m}$  in diameter.

62. The method of claim 49 wherein removing the non-conformal mask material down to the top surface of the first layer includes chemical mechanical polishing.

63. The method of claim 49 wherein removing the conformal mask material above the first layer includes chemical mechanical polishing.

45 64. A method for fabricating a submicron structure on a semiconductor substrate having an oxide layer over the semiconductor substrate and a polysilicon layer over the oxide layer, comprising:

depositing a first layer on top of the polysilicon layer;

forming an opening in the first layer;

depositing a non-conformal material over the first layer to form a void in the trench;

50 removing the non-conformal material down to a top surface of the first layer to expose the void;

depositing a conformal mask material over the first layer and void;

55 removing the conformal mask material above the first layer; and

etching the first layer and non-conformal material.

65. The method of claim 64 wherein the first layer is a mask oxide.

66. The method of claim 64 wherein the non-conformal material is selected from the group consisting of silicon oxide and silicon nitride.

67. The method of claim 64 wherein depositing the non-conformal material includes deposition to a thickness of between 0.3 and 0.45  $\mu\text{m}$ .

68. The method of claim 64 wherein the conformal mask material is polysilicon.

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69. *The method of claim 64 wherein removing the non-conformal mask material down to the top surface of the first layer includes chemical mechanical polishing.*

70. *The method of claim 64 wherein removing the conformal mask material above the first layer includes chemical mechanical polishing.*

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71. *The method of claim 64 wherein etching the first layer and non-conformal material includes an anisotropic etch.*

72. *The method of claim 64 wherein etching the first layer and non-conformal material includes an isotropic etch.*

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